

AMENDMENTS TO THE CLAIMS

1-4. (Canceled)

5. (Currently Amended) An unsymmetrical semiconductor device using a self-aligned contact hole, the device comprising:

a substrate having ~~impurity regions formed~~ a first source/drain region and a second source/drain region therein, wherein the first source/drain region and the second source/drain region have different ion concentrations;

a first ~~conductor structure gate~~ and a second ~~conductor structure gate~~ formed on the substrate;

first sidewall spacers, each first sidewall spacer being formed to abut against ~~both a one~~ one side of the first ~~or and~~ and second ~~conductor structures gates~~ and a one side of an insulator structure such that a vertical portion of each sidewall spacer abuts the ~~conductor structures gates~~, the first sidewall spacers manifesting the self-aligned contact hole in the region between the first and second ~~conductor structures gates~~, ~~wherein the self-aligned contact hole does not overlap any part of the first and second conductor structures~~; and

second sidewall spacers formed on the other sides of the first and second ~~conductor structures gates~~ opposite of to the self-aligned contact hole.

6. (Canceled)

7. (Currently Amended) The unsymmetrical semiconductor device of claim 6, further comprising:

a contact plug formed in the self-aligned contact hole, the contact plug being in contact with the first sidewall spacers and the first ~~impurity~~ source/drain region.

8. (Original) The unsymmetrical semiconductor device of claim 7, wherein the contact plug is also in contact with a bit line.

9. (Currently Amended) The unsymmetrical semiconductor device of claim 7, wherein the contact plug is not disposed directly above the first and second ~~conductor structures~~ gates.